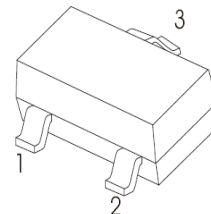


SOT-23 Plastic-Encapsulate Transistor

BC856A, B TRANSISTOR (PNP)

SOT-23
BC857A, B, C
BC858A, B, C

1. BASE
2. EMITTER
3. COLLECTOR



FEATURES

- Low current.(max.100mA)
- Low voltage.(max.65v)

PACKAGE SPECIFICATIONS

Package	Reel Size	Reel DIA. (mm)	Q'TY/Reel (pcs)	Box Size (mm)	QTY/Box (pcs)	Carton Size (mm)	Q'TY/Carton (pcs)
SOT-23	7'	330	3000	190×190×190	45000	400×400×220	180000

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage		V
		BC856	
		BC857	
		BC858	
V _{CEO}	Collector-Emitter Voltage		V
		BC856	
		BC857	
		BC858	
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current –Continuous	-0.1	A
P _{C*}	Collector Power Dissipation	250	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-65-150	°C

DEVICE MARKING

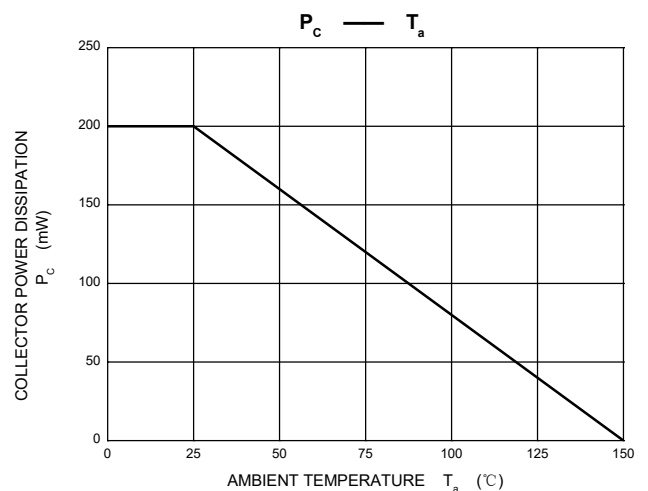
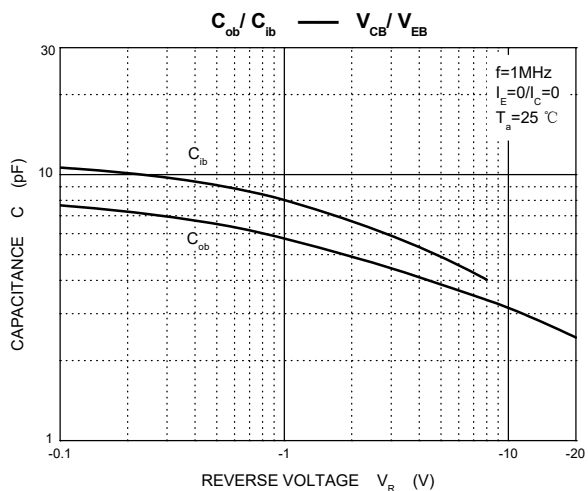
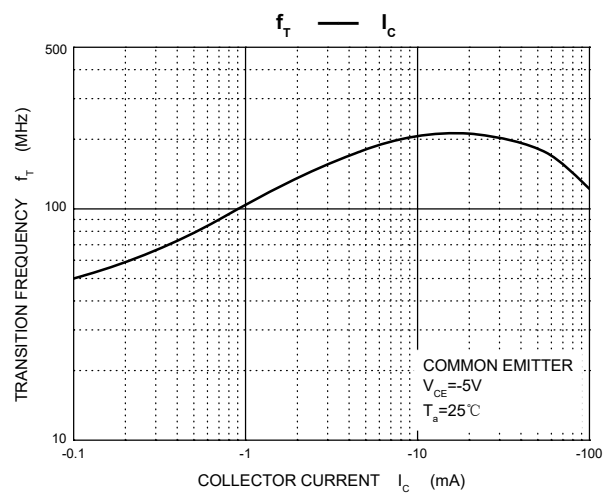
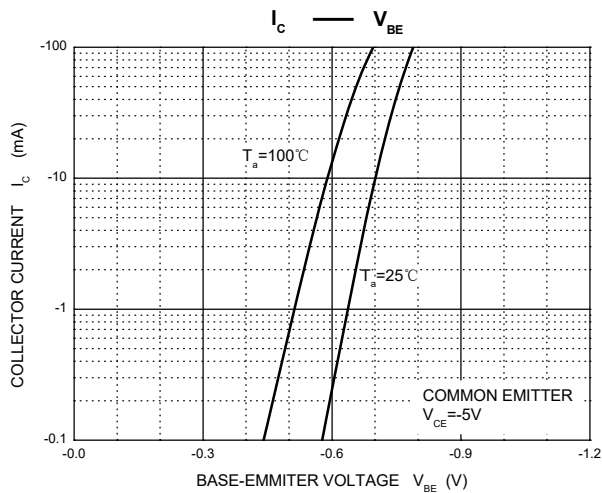
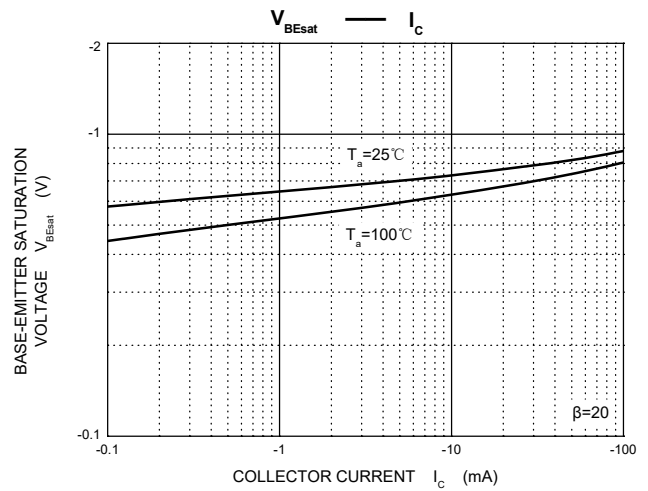
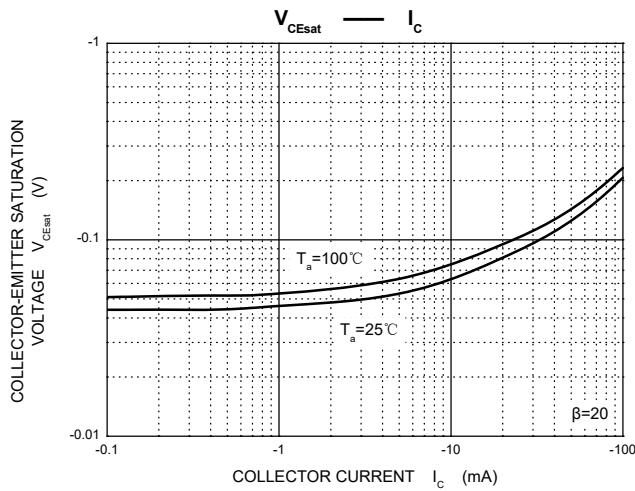
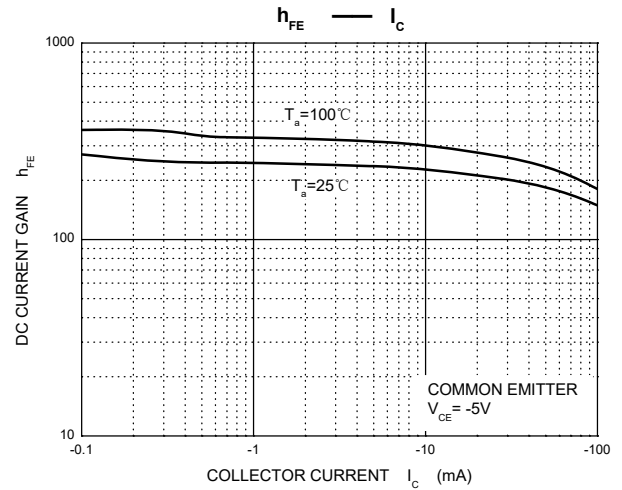
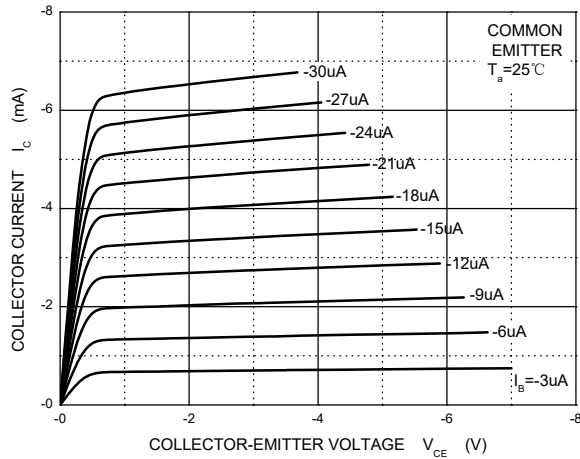
BC856A=3A; BC856B=3B;
 BC857A=3E; BC857B=3F; BC857C=3G;
 BC858A=3J; BC858B=3K; BC858C=3L

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage BC856 BC857 BC858	V _{CBO}	I _C = -10μA, I _E =0	-80 -50 -30		V
Collector-emitter breakdown voltage BC856 BC857 BC858	V _{CEO}	I _C = -10mA, I _B =0	-65 -45 -30		V
Emitter-base breakdown voltage	V _{EBO}	I _E = -1μA, I _C =0	-5		V
Collector cut-off current BC856 BC857 BC858	I _{CBO}	V _{CB} = -70 V, I _E =0 V _{CB} = -45 V, I _E =0 V _{CB} = -25 V, I _E =0		-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5 V, I _C =0		-0.1	μA
DC current gain BC856A, 857A,858A BC856B, 857B,858B BC857C,BC858C	h _{FE}	V _{CE} = -5V,I _C = -2mA	125 220 420	250 475 800	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA,I _B = -5 mA		-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -100mA, I _B = -5mA		-1.1	V
Transition frequency	f _T	V _{CE} = -5 V, I _C = -10mA f=100MHz	100		MHz
Collector capacitance	C _{ob}	V _{CB} =-10V, f=1MHz		4.5	pF

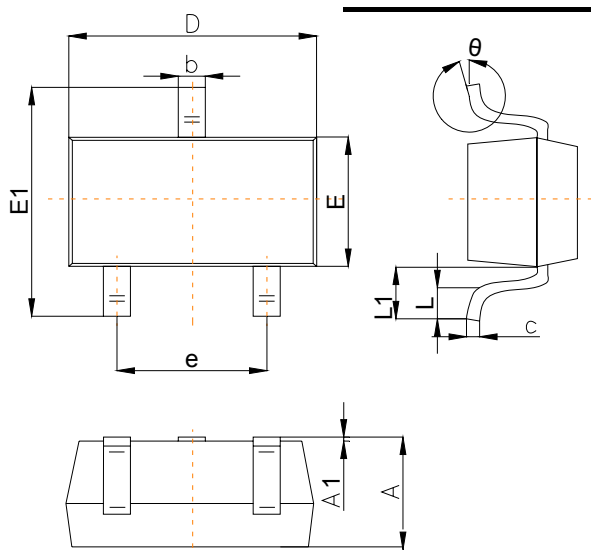
The above data are for reference only.

Typical Characteristics

Static Characteristic


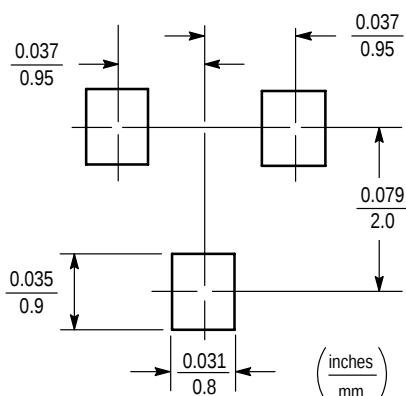
Outline Drawing

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		
	Min	Typ	Max
A	0.65		1.40
A1	0.00		0.20
b	0.30		0.55
c	0.08		0.20
D	2.70		3.10
E	1.15		1.65
E1	2.10		2.80
e	1.70		2.10
L	0.15		0.50
L1	0.35		0.70
θ	0°		12°

Suggested Pad Layout



Note:

1. Controlling dimension: in/millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

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